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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE ATTY. DOCKET NO.

In re Patent Application of Steven E Hiff E

Serial No. 10/761,409

Filed: January 22, 2004

Group Art Unit: 2812

Examiner:

For: DOPED SEMICONDUCTOR NANOCRYSTAL LAYERS AND PREPARATION THEREOF

INFORMATION DISCLOSURE STATEMENT

FEB 2 8 2005

This Information Disclosure Statement is being filed in the manner prescribed by 37 CFR 1.97(b)

- (d) to satisfy the duty under 37 CFR 1.56 to disclose to the Office information, known to individuals associated with the filing and prosecution of the subject application, which is material to the examination of the application.

In accordance with 37 CFR 1.97(g) and (h), this statement is not to be construed as a representation that a search has been made or an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

This Information Disclosure Statement is being filed within three months of the filing date of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first official action on the merits and therefore applicant respectfully requests consideration under 37 CFR 1.97(b).

In compliance with 37 CFR 1.98(a)(2), also enclosed is a legible copy of:

i) each foreign patent.

In compliance with 37 CFR 1.98(a)(1), a list of all patents, publications, applications or other information submitted for consideration by the Office is hereby provided by way of the attached Form PTO-1449.

It is respectfully requested that the information be expressly considered by the Examiner and that

the references be made of record and appear among the "References Cited" on any patent to issue therefrom.

The Patent Office is hereby authorized to charge any deficiency, or credit any overpayment in fees to Deposit Account Number 19-2550.

Respectfully submitted,

STEVEN E. HILL

Dated:

Ralph A. Dowell

Reg. No.26,868

Encls.:

Form PTO-1449

A copy of each reference

(excluding copies of US patent references)

	211.5		
Form PTO-1449 (Modified)	98	Atty. Docket No. 50422-8	Serial No. 10/761,409
LIST OF PATENTS AND PUBLICATIONS	B 2 8 2005	Applicant STEVEN E. HILL	
FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	RADEMARKS	Filing Date January 22, 2004	Group 2812

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

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	AA	5,667,905	1997.09.16	Campisano, Salvatore Ugo et al.			
	AB	6,225,669	2001.07.03	Birkhahn, Ronald H. et al.			
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	AH	101 04 193	2002.08.01	DE					
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AN	Shin, J.H. et al.	CONTROLLING THE QUANTUM EFFECTS AND ERBIUM-CARRIER INTERACTION USING Si/SiO ₂ SUPERLATTICES. Proceedings of the SPIE. Vol. 4282, January 1, 2001. Bellingham, VA United States of America. Pages 142-152.						
AO	Yun, F. et al.	ROOM TEMPERATURE SINGLE-ELECTRON NARROW-CHANNEL MEMORY WITH SILICONNANODOTS EMBEDDED IN SiO ₂ MATRIX. <i>Japanese Journal of Applied Physics</i> . Publication Office Japanese Journal of Applied Physics. Vol. 39, no. 8A Part II. August 1, 2000. Tokyo, Japan. Pages L792- L795.						
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EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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